Characteristics of Final Particles in Multiple Compton Backscattering Process A. Potylitsyn Tomsk Polytechnic University, Tomsk, Russia

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Compton backscattering



Plane - wave approximation

Circularly-polarized wave





Radius of electron trajectory

$$r_{\perp} \sim a_0 \lambda_0$$

MCBS may be treated as undulator radiation in a field of intense plane wave ("light undulator")



$$\begin{array}{l} \text{MCBS process ("light undulator")} \\ K^2 \rightarrow a_0^2, \quad \lambda_U \rightarrow \frac{\lambda_0}{2} \\ \overline{k}_{MCBS} = \frac{2}{3} \pi \alpha a_0^2 l_L, \quad l_L - \text{ length of a laser pulse, } \quad l_L = N_0 \lambda_0 \\ a_0^2 = 4 \pi \alpha \lambda_e^2 \lambda_0 n_0, \\ \hline \lambda_e = \frac{\hbar}{mc}, \quad n_0 - \text{ mean concentration of laser photons.} \\ \overline{k}_{MCBS} = 2 \cdot \frac{8\pi}{3} r_e^2 n_0 l_L = 2\sigma_T n_0 l_L \\ \text{where } \sigma_T = \frac{8\pi}{3} r_e^2 - \text{Thomson cross-section} \\ \text{The strict number of MCBS photons is defined from luminosity} \\ L = c(1 + \beta_0) \sigma N_e N_L \int dV dt F_e(x, z, y, t) F_L(x, y, z, t) \\ N_{e(L)} - \text{ number of electrons (photons) in bunches} \\ F_{e(L)}(x, y, z, t) - \text{ distribution of each bunches in the space and time} \\ \text{Mean number of emitted photons (number of collisions) per electron} \end{array}$$

$$\overline{k}_{MCBS} = \frac{L}{N_e}$$

Mean collision number per each initial electron. (number of photons per particle)



F. Hartemann et al. PRST – AB, (2005)1007 02 $\rho_L^2 = \rho_0^2 (1 + \frac{z^2}{z_R^2}), \quad \rho_e^2 = \rho_b^2 (1 + \frac{z^2}{\beta_f^2}).$

 $\rho_0(\rho_b)$ is the minimum radius of photon (electron) beam. z_R is the Rayleigh length, β_f is the beta function. Longitudinad distributions of beams were approximated by Gaussians with parameters l_L and l_e . In this model the mean number of scattered photons is determined by the flollowing expression :

$$\overline{k} = \frac{16\sqrt{\pi}}{3} \frac{r_e^2}{\rho_0^2} N_L f(l_e, l_L, r), \text{ where}$$

$$f(l_e, l_L, r) = \exp[(1+r^2)/(\mu^2 + r^2\eta^2)]/[(\mu^2 + r^2\eta^2)(1+r^2)]^{1/2} \times \left\{1 - \Phi\left[(1+r^2)^{1/2}/(\mu^2 + r^2\eta^2)^{1/2}\right]\right\},$$

$$\mu = \frac{l_L}{2\sqrt{2}z_R}, \ \eta = \frac{l_e}{2\sqrt{2}\beta_f}, \ r = \frac{\rho_b}{\rho_0}, \ \Phi(x) \text{ is the error function.}$$

Simplest case
$$\rho_{\rm L} = const$$
, $\rho_{\rm e} = const$
In the limit $z_{\rm R} \to \infty$, $\beta_f \to \infty (\mu, \eta \to 0)$
 $1 - \Phi(x) \approx \frac{1}{\sqrt{\pi}} \frac{\exp(-x^2)}{x}$,
 $\overline{k} \approx \frac{16}{3} N_L \frac{r_e^2}{\rho_0^2 + \rho_e^2}$

or using luminosity L : $\overline{k} = \frac{L\sigma}{N_e}$

Introducing a mean photon concentration n_0 and effective length l_L of a laser flash :

$$n_{0} = \frac{N_{L}}{V_{eff}} = \frac{W_{L}}{\hbar\omega_{0}} \frac{1}{\pi \rho_{eff}^{2} l_{L}}:$$

$$\overline{k} \approx l_{L} 2\sigma_{T} (1 - x_{0}) n_{0} \approx \frac{l_{L}}{l_{T}} \text{ for } x_{0} \ll 1, \quad x_{0} \approx \frac{4\gamma_{0} \hbar \omega_{0}}{mc^{2}}$$
Where $l_{T} = \frac{1}{2n_{0}\sigma_{T}} - \text{ so - called Thomson free path electron length in a "light target".$

Scheme for production of polarized positrons

[T. Omori et al. NIMA 500(2003)232]



Number of photons per electron:

 $\overline{k} = 2.4$ CLICHE [D. Asher et al. Eur. Phys. J. C., 28 (2003) 27] $\overline{k} = 1.2$ SAPPHiRE [S. A. Bogacz et. al. arXiv: 1208.2827]

Analytic description of MCBS process

The cross-section of the linear MCBS process

$$\frac{d\sigma}{dy} = \frac{2\pi r_e^2}{x_0} \left[\frac{1}{1-y} + 1 - y - \frac{4y}{x_0(1-y)} \left(1 - \frac{y}{x_0(1-y)} \right) \right],$$
$$x_0 = \frac{2p_0 k_0}{(mc^2)^2} \approx \frac{4\gamma_0 \hbar \omega_0}{mc^2}, \qquad y = 1 - \frac{p_0 k}{p_0 k_0} \approx \frac{\hbar \omega}{\gamma_0 mc^2}$$

MCBS is the stochastic process where \overline{k} and electron energy losses $\Delta \varepsilon = \varepsilon_0 - \varepsilon$

along a path l are described by the probability distribution $P(\varepsilon, \varepsilon_0, l)$

$$\frac{\partial}{\partial l}P(\varepsilon,\varepsilon_0,l) + \Sigma(\varepsilon_0)P(\varepsilon,\varepsilon_0,l) \int_{0}^{\hbar\omega_{\max}} \Sigma(\hbar\omega;\varepsilon_0)P(\varepsilon,\varepsilon_0-\hbar\omega,l)d\hbar\omega = 0$$

with the boundary condition

$$P(\varepsilon,\varepsilon_0,l=0) = \delta(\varepsilon-\varepsilon_0).$$

Here

$$\Sigma(\hbar\omega,\varepsilon_0) = 2\bar{n}_0 \frac{d\sigma}{d\hbar\omega}$$

is the differential macroscopic cross-section of the Compton scattering process and

 $\Sigma(\varepsilon_0) = \int_{0}^{\hbar\omega_{\max}} \Sigma(\hbar\omega;\varepsilon_0) d\hbar\omega = 0 \quad \text{ is the total macroscopic cross-section.}$

In the paper [A.Kolchuzhkin, A. Potylitsyn, S. Strokov et al., Nucl. Instr. and Meth. B 201 (2003) 307] we have derived analytical formulae for the main parameters

$$\overline{k}(\varepsilon_0, l_L) = 2\sigma_T \overline{n_0} l_L - 2\log\left(1 + \frac{g_1(\varepsilon_0)l_L}{\varepsilon_0}\right),$$

$$\overline{\varepsilon}(\varepsilon_0, l_L) = \frac{\varepsilon_0}{1 + g_1(\varepsilon_0)l_L/\varepsilon_0},$$
$$\Delta(\varepsilon_0, l_L) = \frac{g_2(\varepsilon_0)l_L}{\left[1 + g_1(\varepsilon_0)l_L/\varepsilon_0\right]^4}.$$

where coefficients $g_{1,2}(\varepsilon_0)$ are defined as

$$g_{1}(\varepsilon_{0}) = \int_{0}^{\hbar\omega_{\max}} \hbar\omega \Sigma(\hbar\omega;\varepsilon_{0}) d\hbar\omega,$$
$$g_{2}(\varepsilon_{0}) = \int_{0}^{\hbar\omega_{\max}} (\hbar\omega)^{2} \Sigma(\hbar\omega;\varepsilon_{0}) d\hbar\omega.$$

In the case $x_0 \ll 1$

$$\overline{\varepsilon}(\varepsilon_0, l_L) \approx \frac{\varepsilon_0}{1 + \frac{1}{2}\overline{k}x_0 \left(1 - \frac{21}{10}x_0\right)},$$
$$\Delta(\varepsilon_0, l_L) \approx \frac{\frac{7}{20}\overline{k}\varepsilon_0^2 x_0^2}{\left(1 + \frac{1}{2}\overline{k}x_0\right)^4}.$$

Or, substituting n_0 and $\hbar\omega_{max}$ instead \overline{k}

$$\overline{\varepsilon} = \varepsilon_0 (1 - x_0 \sigma_T n_0 l_L) = \varepsilon_0 - \sigma_T n_0 \hbar \omega_{max} l_L,$$
$$\Delta^2 = \frac{7}{20} 2\sigma_T n_0 l_L \varepsilon_0^2 x_0^2 = \frac{7}{10} \sigma_T n_0 (\hbar \omega_{max})^2 l_L.$$

it is possible to compare expressions obtained with results:

[Robb G.R.M., Bonifacio R., Europhys. Lett., 94 (2011) 34002].

The difference is $^{7}/_{10}$ instead 1 in the second expression.

Monte - Carlo simulation

Distribution over the collision number *k* (number of emitted photons)



 $\begin{cases} \sigma_k^2(l) = \overline{k}(l) \text{- main characteristics of the Poisson law} \\ P(n,\overline{k}) = \overline{k}^2 \exp(-\overline{k})/n! \\ \text{For any value of } \overline{k} \text{ there is a part of electrons passing through a light target without interaction } (n = 0): \\ P(0,\overline{k}) = \exp(-\overline{k}) \\ \text{For } \overline{k} = 1, \exp(-\overline{k}) = 0.37 = 37\% \end{cases}$

A random path length and a random energy loss were successively simulated in each collision



 $\overline{k} = \sigma_k^2$ for small x_0 and small thickness - typical characteristic of Poisson law

Energy distribution of recoil electrons

for small collision number $(\overline{k} = 0.5)$



Energy distribution of beam passed through a light target



Analitical solution are valid for $x_0 \ll 1$ (see Kolchuzhkin et al. NIMB 201 (2003) 307)

Energy distribution of electron beam passed through a light target



Energy distribution of electron beam passed through a light target



Photon spectra as a result of MCBS process



Energy distribution of electron beam at the undulator exit



Spin-dependent cross section

Unpolarized e^+ beam may be considered as a sum of two polarized components with a half of the initial intensity and polarized in opposite directions (indice + means parallel orientation of positron spin and momentum, + - antiparallel one)

In this case for
$$P_c = +1$$
, $|\xi_z| = |\xi_{z0}| = 1$

$$\frac{d\sigma_{+}}{dy} = \frac{d\sigma_{++}}{dy} + \frac{d\sigma_{+-}}{dy} = 2\left(\frac{d\sigma_{0}}{dy} + \frac{d\sigma_{1}}{dy}\right)$$
$$\frac{d\sigma_{-}}{dy} = \frac{d\sigma_{--}}{dy} + \frac{d\sigma_{-+}}{dy} = 2\left(\frac{d\sigma_{0}}{dy} - \frac{d\sigma_{1}}{dy}\right)$$

where

$$\frac{d\sigma_{++}}{dy} = \frac{d\sigma_0}{dy} + \frac{d\sigma_1}{dy} + \frac{d\sigma_2}{dy} + \frac{d\sigma_3}{dy}; \quad \text{non spin - flip term}$$
$$\frac{d\sigma_{+-}}{dy} = \frac{d\sigma_0}{dy} + \frac{d\sigma_1}{dy} - \frac{d\sigma_2}{dy} - \frac{d\sigma_3}{dy}; \quad \text{spin - flip term}$$
$$\frac{d\sigma_{--}}{dy} = \frac{d\sigma_0}{dy} - \frac{d\sigma_1}{dy} - \frac{d\sigma_2}{dy} + \frac{d\sigma_3}{dy}; \quad \text{non spin - flip term}$$
$$\frac{d\sigma_{-+}}{dy} = \frac{d\sigma_0}{dy} - \frac{d\sigma_1}{dy} + \frac{d\sigma_2}{dy} - \frac{d\sigma_3}{dy}; \quad \text{spin - flip term}$$

For unpolarized beam (after averaging over initial polarization states).

$$\frac{d\sigma_{unp}}{dy} = 2\frac{d\sigma_0}{dy} \approx \frac{\pi r_0^2}{x_0} \left\{ \frac{1}{1-y} + 1 - y - s^2 \right\}$$
$$\hbar \omega_{max} = \gamma_0 mc^2 \frac{x_0}{1+x_0}$$



 $\hbar\omega_{\rm max} = 803.546 \,{\rm MeV}$

 $\hbar\omega_{\rm max} = 32846.3 \,{\rm MeV}$

Comparison of both parts of cross-section for different electron energies



It is evidently for any electron energy

$$\frac{d\sigma_{+-}}{dy} = \frac{d\sigma_{-+}}{dy}$$

within an accuracy γ_0^{-1} .

It means there is no polarisation of the final beam as whole.

But for the case when each positron in a beam will interact with *CP* laser photons a few times (<u>multiple Compton backscattering process</u>) the final positron beam will have the non - zeroth polarization for a part of beam due to difference in cross - sections :

$$\frac{d\sigma_{+}}{dy} \neq \frac{d\sigma_{-}}{dy}$$





Initial electron energy 50 GeV





Summary

- Distribution over number of emitted photons describes by Poisson law with a good accuracy
- In the MCBS process (and for ordinary UR also but not for FEL) the final distribution of electrons is continuos, which may be described by gaussian one. KS TOT YOUR ATTENTION.
- Even for small mean number of collisions (<k>~1) there is significant contribution of events with k = 2,3... photons from each electron/positron
- The ordinary multiple Compton backscattering process (plane wave approximation) may provide polarization of a part of unpolarized beam
- For the case $x_0 \ge 0.1$ a resulting photon spectrum is distorted significantly if $\overline{k}_{MCBS} \gg 1$ in comparison with a single photon spectrum